



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



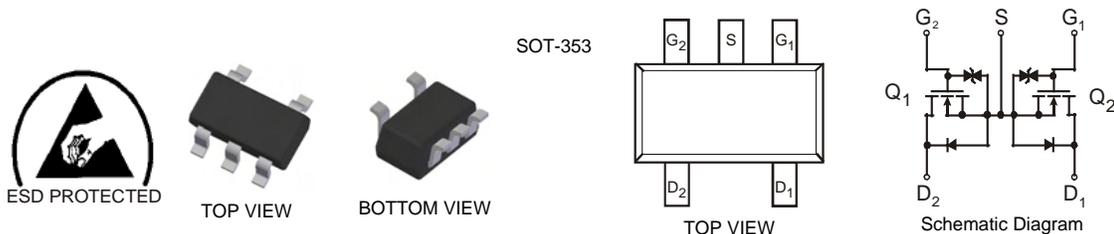
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Features

- Common Source Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.2V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Small Surface Mount Package
- ESD Protected Gate

Mechanical Data

- Case: SOT-353
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)



Maximum Ratings Q_1, Q_2 @ $T_A = 25^\circ\text{C}$ unless otherwise specified

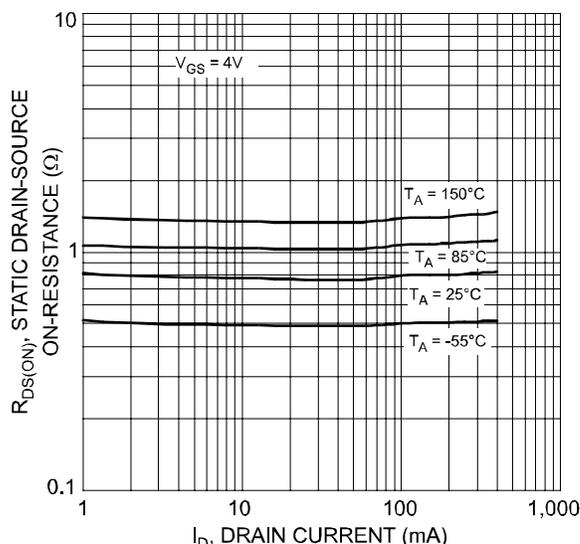
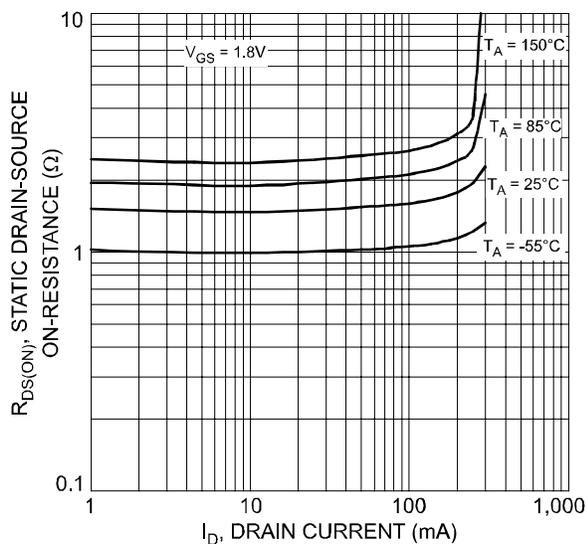
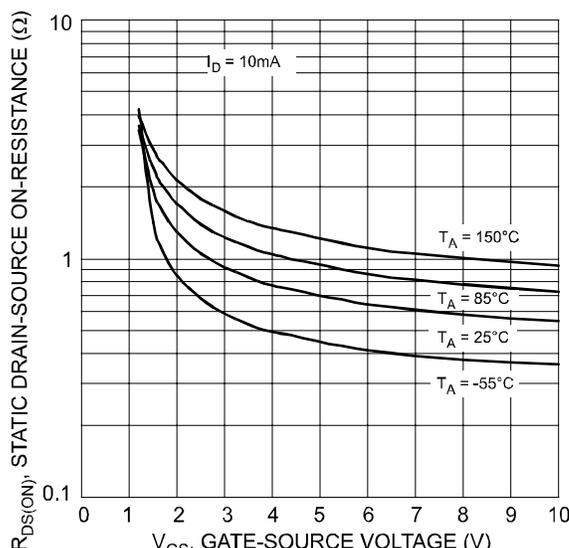
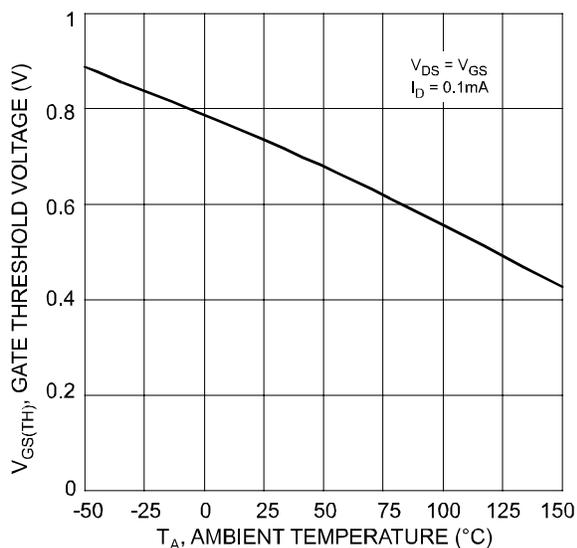
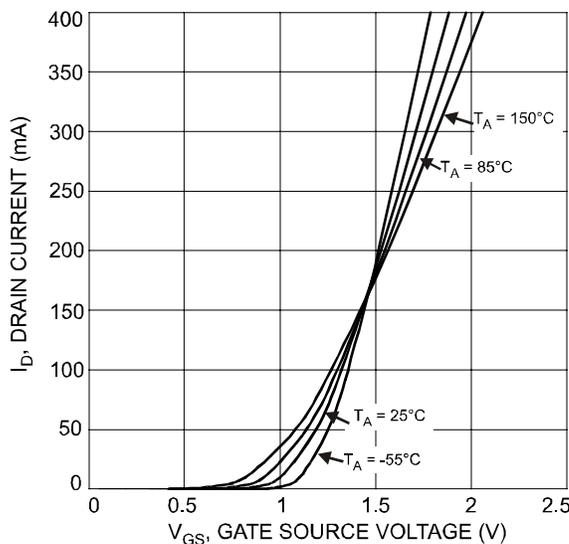
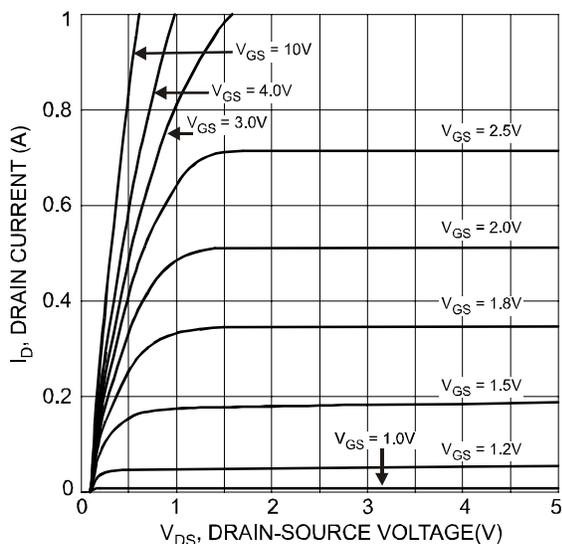
Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	± 10	V
Drain Current (Note 1)	I_D	400	mA

Thermal Characteristics Q_1, Q_2 @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Total Power Dissipation (Note 1)	P_D	280	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	446	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics Q_1, Q_2 @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current @ $T_C = 25^\circ\text{C}$	I_{DSS}	—	—	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Body Leakage	I_{GSS}	—	—	± 10 ± 1	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$ $V_{GS} = \pm 5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	$V_{GS(th)}$	0.6	—	1.2	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	2.2 1.5 1.2	Ω	$V_{GS} = 1.8V, I_D = 20\text{mA}$ $V_{GS} = 2.5V, I_D = 20\text{mA}$ $V_{GS} = 4.0V, I_D = 100\text{mA}$
Forward Transconductance	$ Y_{fs} $	100	—	—	mS	$V_{DS} = 10V, I_D = 0.1A$
Source-Drain Diode Forward Voltage	V_{SD}	0.5	—	1.4	V	$V_{GS} = 0V, I_S = 115\text{mA}$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	39	—	pF	$V_{DS} = 3V, V_{GS} = 0V$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	10	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	3.6	—	pF	
Switching Time	Turn-on Time	t_{on}	—	11	nS	$V_{DD} = 5V, I_D = 10\text{mA},$ $V_{GS} = 0-5V$
	Turn-off Time	t_{off}	—	51	nS	



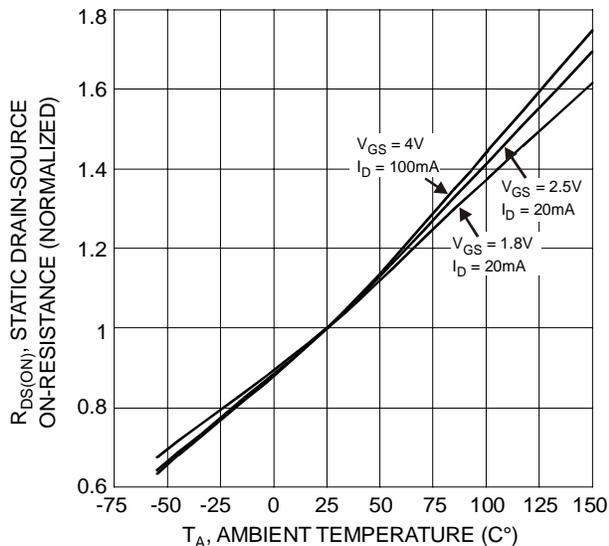


Fig. 7 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

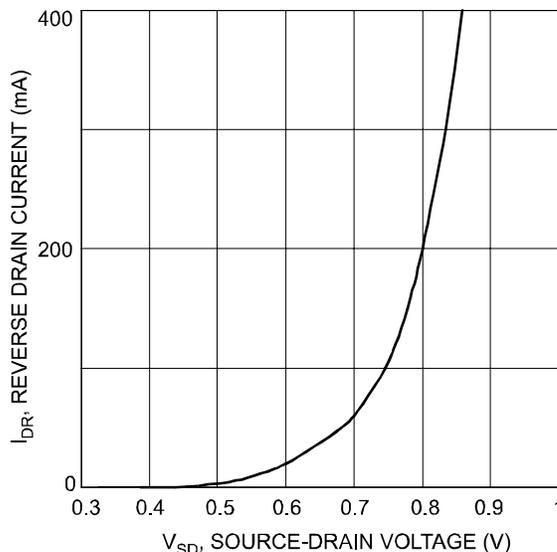


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

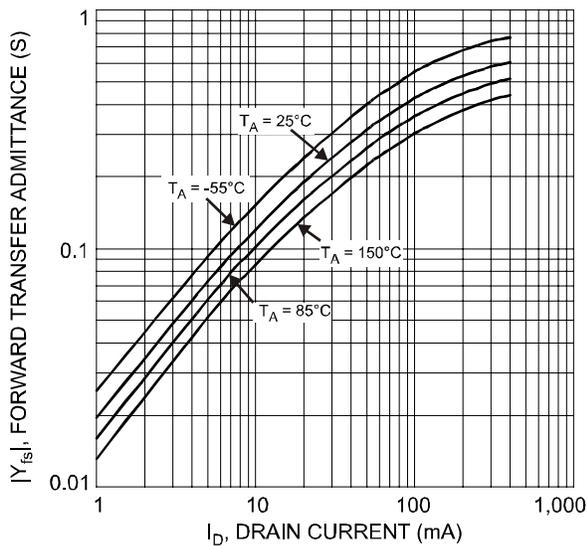


Fig. 9 Forward Transfer Admittance vs. Drain Current

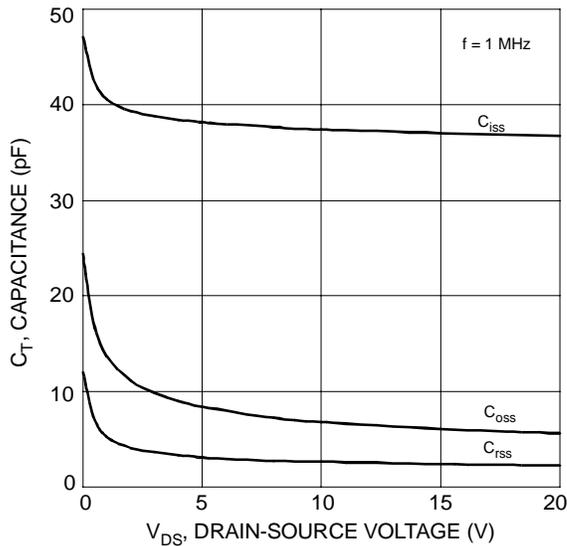
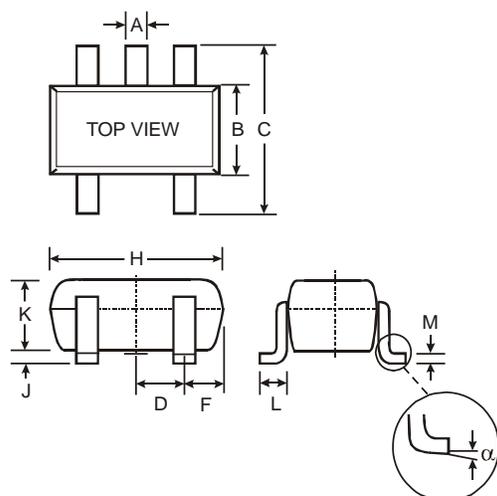


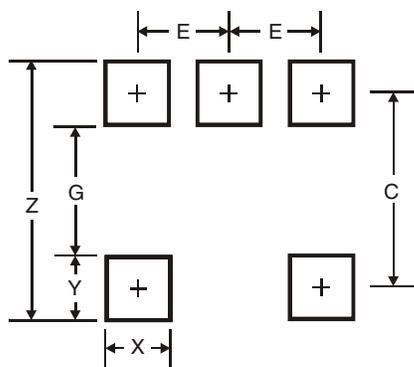
Fig. 10 Typical Capacitance

Package Outline Dimensions



SOT-353		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C	1.9
E	0.65